



ALD 2014 2nd Call for Abstract

14th International Conference on Atomic Layer Deposition

June 15 - 18, 2014, Kyoto, Japan

The AVS Topical Conference on Atomic Layer Deposition 2014 (ALD 2014) will be a three-day meeting, (preceded by one day of workshop) dedicated to the science and technology of atomic layer controlled deposition of thin films. In every year since 2001 at Monterey, the conference had been held alternatively in United States, Europe, and Asia allowing fruitful exchanges of scientists' ideas, know-hows, and practices.

Atomic Layer Deposition (ALD) is used to fabricate ultrathin and conformal thin film structures for many semiconductor and thin film device applications. A unique attribute of ALD is that it uses sequential self-limiting surface reactions to achieve control of film growth in the monolayer or sub-monolayer surface thickness regime. ALD is receiving attention for its potential applications from semiconductor leading-edge technologies, advanced microsystems, displays to energy capture and storage, solid state lighting, biotechnologies, and security. ALD is particularly advantageous for any advanced technologies that require control of film structure in the nanometer or sub-nanometer scale.

This conference offers an excellent opportunity to learn about the most recent R&D activities in ALD science and technology from researchers around the world. We look forward to your attendance.

**ALD 2014 Co-Chair: Yukihiro SHIMOGAKI (The University of Tokyo)
Christian DUSSARRAT (Air Liquide)**

Session Categories

1. ALD Fundamentals

a) Precursors & Chemistry

Precursor Design, Precursor Delivery Systems, ALD Recipe Development, Simulation, Modeling, Theory of ALD

b) Growth & Characterization

In-Situ Monitoring & Analysis, ALD Surface Chemistry & Initiation of ALD Growth, Surface Preparation for ALD, Characterization of ALD Coatings, Highly Conformal ALD Processes

c) Novel Materials

Molecular Layer Deposition, Organic-Inorganic Hybrid Materials, Atomic Layer Epitaxy & Doping

2. ALD Applications

a) Energy Applications

Catalysis and Fuel Cells, Solar Photovoltaic and Photocatalytic, Batteries and Storage

b) ULSI FEOL Applications

High-k and Related Device Applications, Gate Electrode, Contact Metal, 3D-Transistor Fabrication

c) ULSI BEOL Applications

Interconnect Technologies, Cu-Diffusion Barrier Layer, Cu-Capping Technologies, Low-k Pore Sealing

d) Memory Applications

DRAM Capacitor Fabrication, High-k Dielectrics, High Work Function Electrode, Novel Non-Volatile Memories

e) Emerging Applications

MEMS/NEMs, Biotechnologies (Anti-bacterial Films, Medical Devices), Lighting & Display, Magnetic Materials, Nano Structure Synthesis and Fabrication, Nano-Laminates, Nanotubes, Nanowires, Nanopores, Nanoparticles

3. ALD for Manufacturing

a) Reactor and Equipment Design

Design for Manufacturing, ALD Reactor Modeling & Simulation, Patterned & Selective Area ALD, ALD Integration with Conventional Processes

b) Large Format ALD

Spatially Controlled ALD, Fast ALD, R2R

Dates

Workshop June 15, 2014 (Sun)

Conference June 16 (Mon) - 18 (Wed), 2014

Important Dates

Abstract Preparation and Submission: ~~January 6 - February 14, 2014~~ February 28, 2014 (Extended)

Notification of Acceptance to the authors: April 1, 2014

Early Registration: March 14 - May 7, 2014

Abstract Submission and Formatting Guidelines

Abstracts are due: ~~February 14, 2014~~ February 28, 2014 (Extended)

Prospective authors are invited to **submit online**. Abstracts should be **no more than one page**, including figures, in **Adobe PDF format**. Abstracts should be formatted in Arial and include in the following order:

- Title (Arial, 14 pt bold, centered, title case), followed by,
- Presenting author and co-author affiliation, city, and country. Be sure to include the presenting author's e-mail. (Arial, 11 pt, centered)
- Abstract body (Arial, 10 pt)

In addition, the submission website will provide instructions for uploading your abstract, please review those details. When submitting abstracts, authors should create an account on the website. Presenting author and co-author informations should be registered. 1st and 2nd choices of session categories should be selected. A template of abstract can be downloaded from the ALD 2014 website. Notification of acceptance will be made to the authors by April 1, 2014. Upon notification, authors will be requested to confirm their participation in the conference. The accepted abstracts will be included in the booklet that the participants will receive on site at the registration desk of ALD 2014. As in past conferences, the presentations will follow an all-electronic format, and electronic copies of the presentations (including oral component, and questions and answers) will be made available in the form of copy-secured DVDs.

Conference Web Site

<http://www.ald2014.org>

Contact

E-mail: sec@ald2014.org

Location, Conference Venue

Hotel Granvia Kyoto

<http://www.granviakyoto.com>

Map & Transportation to Hotel Granvia Kyoto

Hotel Granvia Kyoto is directly connected to JR (Japan Railway) Kyoto station. To access Kyoto station, Osaka / Kansai International Airport (KIX) is the most convenient one.



Osaka / Kansai International Airport (KIX) (Distance: 97km/60 miles South West of the Hotel)

From KIX to the Hotel:

Terminal-to-terminal train ride of 80 min. by Haruka Express Train from Kansai Airport Station to Kyoto Station. Ticket: JPY4,010 for Green Car (premier reserved), JPY3,280 for standard reserved, JPY2,770 for non-reserved one way
90 min. by Airport Limousine from Kansai Airport to Kyoto Station (Hachijo-guchi, on the south side of the station). Fare: JPY2,600 one way, or JPY4,000 round trip
90 min. by taxi approx. at JPY20,000